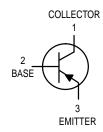
Amplifier Transistor PNP Silicon



MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCEO	-60	Vdc	
Collector-Base Voltage	V _{CBO}	-60	Vdc	
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc	
Collector Current — Continuous	IC	-600	mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C	

THERMAL CHARACTERISTICS

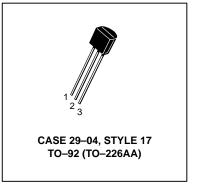
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Characteristic	Symbol	IVIIII	IVIAX	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ⁽¹⁾ (IC = -10 mAdc, I _B = 0)	V(BR)CEO	-60	_	Vdc
Collector-Base Breakdown Voltage (IC = $-10 \mu Adc$, IE = 0)	V _(BR) CBO	-60	_	Vdc
Emitter–Base Breakdown Voltage ($I_C = -10 \mu Adc, I_C = 0$)	V(BR)EBO	-5.0	_	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	ICEX	_	- 50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I _{CBO}	_ _	-0.01 -10	μAdc
Emitter Cutoff Current (VEB = -3.0 Vdc)	I _{EBO}	_	-10	nAdc
Collector Cutoff Current $(V_{CE} = -10 \text{ V})$	ICEO	_	-10	nAdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{BEX}	_	- 50	nAdc

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.







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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

	Characteristic	Symbol	Min	Max	Unit
ON CHARACTER	STICS	•			
	V _{CE} = −10 Vdc)	hFE	75 100 100 100 50	 300 	_
Collector-Emitter S (I _C = -150 mAdc, (I _C = -500 mAdc,	$I_B = -15 \text{ mAdc}$	VCE(sat)	_ _ _	-0.4 -1.6	Vdc
Base-Emitter Satur ($I_C = -150 \text{ mAdc}$, ($I_C = -500 \text{ mAdc}$,	$I_B = -15 \text{ mAdc}$	VBE(sat)	— —	-1.3 -2.6	Vdc
SMALL-SIGNAL	CHARACTERISTICS			-	-
	indwidth Product ⁽¹⁾ , (2) CE = -20 Vdc, f = 100 MHz)	fτ	200	_	MHz
Output Capacitance (V _{CB} = -10 Vdc,	E = 0, f = 1.0 MHz)	C _{obo}	_	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc,	I _C = 0, f = 1.0 MHz)	C _{ibo}	_	30	pF
SWITCHING CHA	RACTERISTICS	•			
Turn-On Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$ $I_{B1} = -15 \text{ mAdc}) \text{ (Figures 1 and 5)}$	t _{on}	_	50	ns
Delay Time		t _d	_	10	ns
Rise Time		t _r		40	ns
Turn-Off Time	$(V_{CC} = -6.0 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$ $I_{B1} = I_{B2} = -15 \text{ mAdc}) \text{ (Figure 2)}$	t _{off}	_	110	ns
Storage Time		t _S	_	80	ns
Fall Time		t _f	_	30	ns

- 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

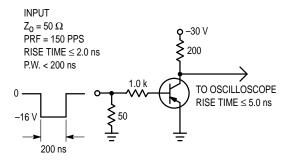


Figure 1. Delay and Rise Time Test Circuit

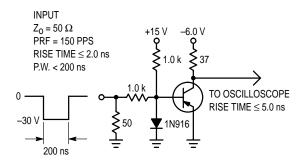


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

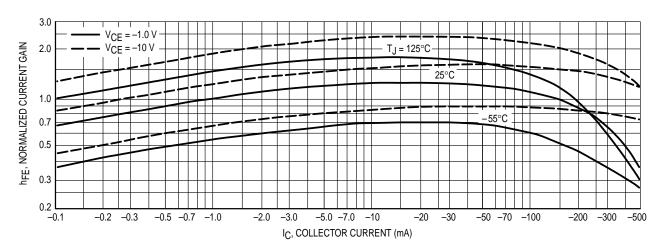


Figure 3. DC Current Gain

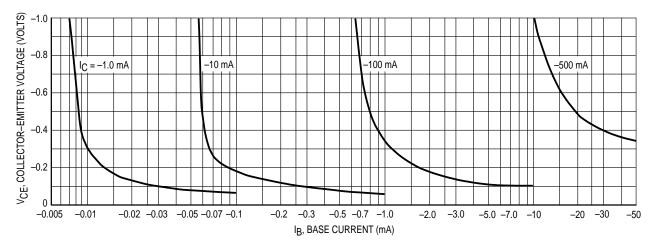


Figure 4. Collector Saturation Region

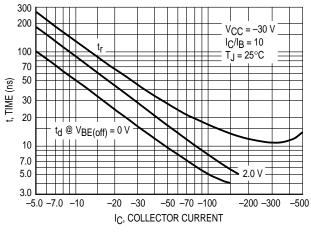


Figure 5. Turn-On Time

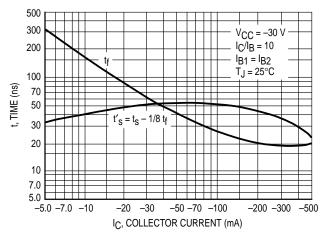


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS **NOISE FIGURE**

V_{CE} = 10 Vdc, T_A = 25°C

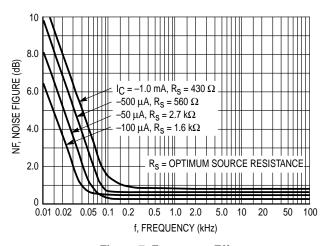


Figure 7. Frequency Effects

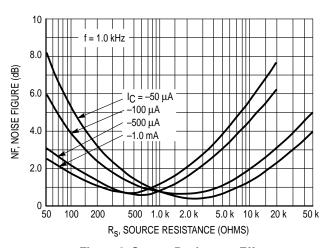


Figure 8. Source Resistance Effects

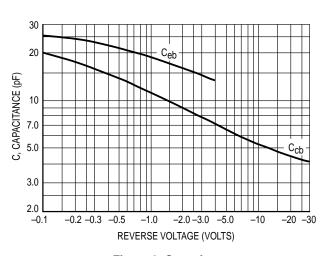


Figure 9. Capacitances

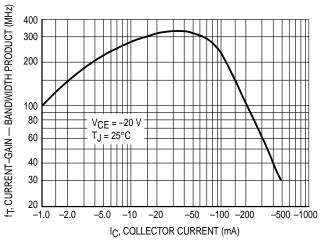


Figure 10. Current-Gain — Bandwidth Product

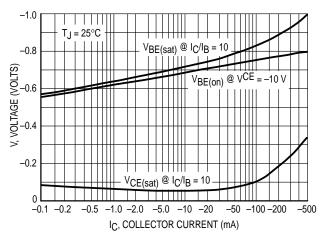


Figure 11. "On" Voltage

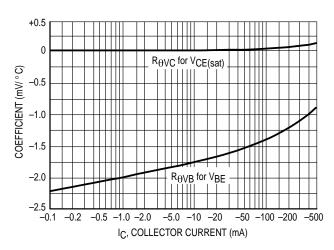
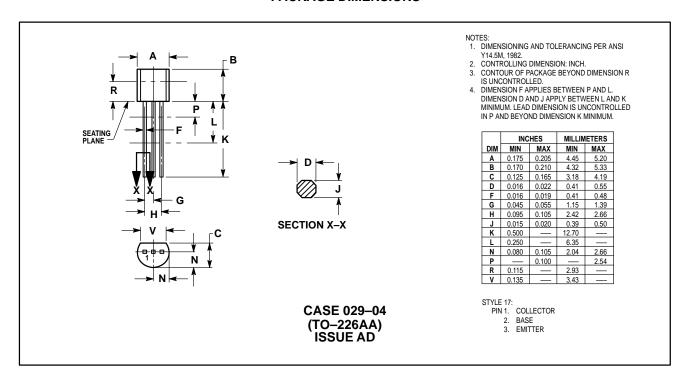


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS



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